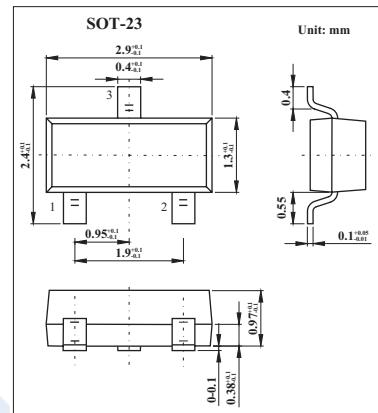
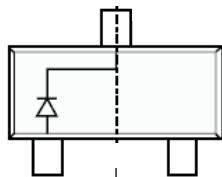


## 0.75 Surface Mount Schottky Barrier Rectifier

### KAT750(BAT750)

#### ■ Features

- Very Low Forward Voltage Drop
- High Conductance
- For Use in DC-DC Converter, PCMCIA, and Mobile Telecommunications Applications



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Peak repetitive reverse voltage	V <sub>RRM</sub>		
Working peak reverse voltage	V <sub>RWM</sub>	40	V
DC blocking voltage	V <sub>R</sub>		
RMS reverse voltage	V <sub>R(RMS)</sub>	28	V
Average rectified output current	I <sub>O</sub>	0.75	A
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	5.5	A
Power dissipation	P <sub>D</sub>	350	mW
Typical Thermal Resistance Junction to Ambient	R <sub>θJA</sub>	286	°C/W
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-40 to +125	°C

#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V <sub>(BR)R</sub>	I <sub>R</sub> = 300 μ A	40	45		V
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 50mA		225	280	
		I <sub>F</sub> = 100mA		235	310	
		I <sub>F</sub> = 250mA		290	350	
		I <sub>F</sub> = 500mA		340	420	mV
		I <sub>F</sub> = 750mA		390	490	
		I <sub>F</sub> = 1000mA		420	540	
		I <sub>F</sub> = 1500mA		475	650	
Leakage current	I <sub>R</sub>	V <sub>R</sub> = 15V		50	100	μ A
Junction Capacitance	C <sub>J</sub>	V <sub>R</sub> = 0, f = 1.0MHz		175		pF
		V <sub>R</sub> = 25V, f = 1.0MHz		25		

#### ■ Marking

Marking	K77 or K79
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